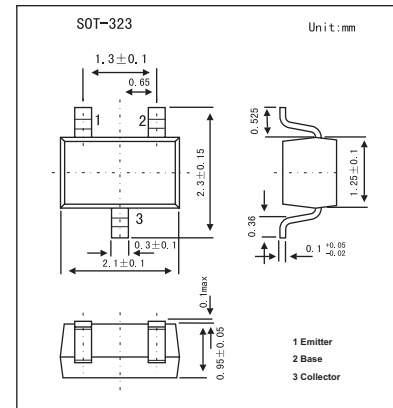


PNP General Purpose Transistor

BC859W,BC860W

■ Features

- Low current (max. 100 mA).
- Low voltage (max. 45 V).

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	BC859W	BC860W	Unit
Collector-base voltage	V_{CB0}	-30	-50	V
Collector-emitter voltage	V_{CE0}	-30	-45	V
Emitter-base voltage	V_{EB0}	-5		V
Collector current	I_C	-100		mA
Peak collector current	I_{CM}	-200		mA
Peak base current	I_{BM}	-200		mA
Total power dissipation	P_{tot}	200		mW
Junction temperature	T_j	150		$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +150		$^\circ\text{C}$
Operating ambient temperature	R_{amb}	-65 to +150		$^\circ\text{C}$
Thermal resistance from junction to ambient	$R_{th\ j-a}$	625		K/W

BC859W,BC860W

■ Electrical Characteristics Ta = 25°C

Parameter		Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current		ICBO	IE = 0; VCB = -30 V			-15	nA
		ICBO	IE = 0; VCB = -30 V; Tj = 150 °C			-4	μA
Emitter cutoff current		IEBO	IC = 0; VEB = -5 V			-100	nA
DC current gain	BC859W; BC860W	hFE	IC = -2 mA; VCE = -5 V;	220		800	
	BC859BW; BC860BW			220		475	
	BC859CW; BC860CW			420		800	
Collector-emitter saturation voltage		VCE(sat)	IC = -10 mA; IB = -0.5 mA			-300	mV
			IC = -100 mA; IB = -5 mA;			-650	mV
Base-emitter voltage *2		VBE	IC = -2 mA; VCE = -5 V	600		750	mV
			IC = -10 mA; VCE = -5 V			820	mV
Collector capacitance		Cc	IE = ie = 0; VCB = -10 V; f = 1 MHz			5	pF
Emitter capacitance		Ce	IC = ic = 0; VEB = -500 mV; f = 1 MHz		10		pF
Transition frequency		fT	IC = -10 mA; VCE = -5 V; f = 100 MHz	100			MHz
Noise figure	BC859W; BC860W; BC859BW; BC860BW; BC859CW; BC860CW	NF	IC = -200 μA; VCE = -5 V; Rs = 2 kΩ; f = 10 Hz to 15.7 kHz			4	dB
			IC = -200 μA; VCE = -5 V; Rs = 2 kΩ; f = 1 kHz; B = 200 Hz			4	

*1. VBEsat decreases by about -1.7 mV/K with increasing temperature.

*2. VBE decreases by about -2 mV/K with increasing temperature.

■ hFE Classification

TYPE	BC859W	BC859BW	BC859CW
Marking	4D	4B	4C

TYPE	BC860W	BC860BW	BC860CW
Marking	4H	4F	4G